

SANYO Semiconductors DATA SHEET

SBR50-16JS — Schottky Barrier Diode (Twin Type · Cathode Common) 160V, 5A Rectifier

Applications

• High frequency rectification (switching regulators, converters, choppers).

Features

- Tj=150°C.
- Low forward voltage (VF max=0.80V).
- Short reverse recovery time.
- Low switching noise.
- High reliability due to planar structure.
- · Attachment workability is good by Mica-less package.

Specifications

Absolute Maximum Ratings at Ta=25°C

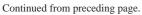
Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		160	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		165	V
Average Output Current	IO	50Hz resistive load, Sine wave Tc=128°C	5	А
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	80	А
Junction Temperature	Tj		-55 to +150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Reverse Voltage	VR	I _R =1mA, Tj=25°C*	160			V
Forward Voltage	VF	IF=2.5A, Tj=25°C*		0.77	0.80	V
Reverse Current	IR	V _R =160V, Tj=25°C*		2.5	50	μΑ
Note) * : Value per element Continued on next						next page.

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Interterminal Capacitance	С	V _R =10V, Tj=25°C*		48		pF
Thermal Resistance	Rth(j-c)	Junction-Case : Smoothed DC			5.0	°C / W

Note) * : Value per element

Package Dimensions

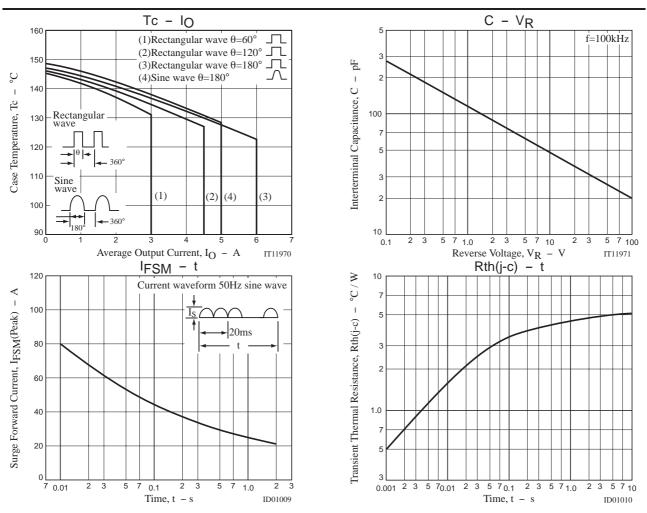
unit : mm (typ) 7525-001

10.0 4.5 Ø3.2 2.8 3.5 ŧ Cathode 0 16.0 0 3.6 6 14.0 0.7 1 : Anode 2 : Cathode 3 : Anode SANYO : TO-220ML(LS) IF - VF IR - VR 10 10 7 7 Tj=150°C ty 5 5 3 2 Reverse Current, IR - mA Forward Current, IF - A 3 1.0 125°C typ 2 c_{b_p} Cth 7 5 1.0 3 52. 100°C typ 2 7 5 0.1 3 75°C typ 5 3 2 2 0.01 0.1 60 80 100 120 Reverse Voltage, V_R – V 0.2 0 0.4 0.6 0.8 1.0 1.2 0 20 40 140 160 180 Forward Voltage, V_F - V PF(AV) - IO IT11966 IT11967 PR(AV) - VRM Average Forward Power Dissipation, Pp(AV) - W Average Reverse Power Dissipation, PR(AV) - W 6 1.2 (1)Rectangular wave θ =300° \Box Sine wave (2)Rectangular wave θ =240° ப (3) 1.0 (3)Rectangular wave $\theta = 180^{\circ}$ (1)5 ப 180° (4)Sine wave $\theta = 180^{\circ}$ 360° (4)0.8 Rectangular wave (2)4 Rectangular (2)۲ VR (3) 3 0.6 -θ+ → 360° < Sine wave 0.4 2 (1)Rectangular wave $\theta = 60^{\circ}$ (2)Rectangular wave $\theta = 120^{\circ}$ (4) 0.2 (3)Rectangular wave $\theta = 180^{\circ}$ Λ (4)Sine wave $\theta = 180^{\circ}$ 0 L 0 0 3 4 5 100 120 2 6 20 60 80 140 160 180 40 Average Output Current, IO - A Peak Reverse Voltage, $V_{RM} - V$ IT11968 IT11969

Electrical Connection

Anode

Anode



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